NSN 5961-01-100-8575

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View Online at https://aerobasegroup.com/nsn/5961-01-100-8575 **Inclosure Material:** Metal **Overall Length:** Between 0.170 inches and 0.210 inches **Terminal Length:** Between 0.500 inches and 0.750 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-18 **Electrode Internally-electrically Connected To Case:** Gate **Mounting Method: Terminal Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 drain to gate voltage and 30.0 drain to source voltage and 30.0 gate to source voltage **Current Rating Per Characteristic:** 50.00 milliamperes gate current **Power Rating Per Characteristic:** 0.5 watts total power dissipation **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 3 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/476 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:**

No

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